



# NCE N-Channel Enhancement Mode Power MOSFET

#### Description

The NCE40H12K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

- V<sub>DS</sub> =40V,I<sub>D</sub> =120A
  R<sub>DS(ON)</sub> <4.0mΩ @ V<sub>GS</sub>=10V
  - $R_{DS(ON)}$  <7m $\Omega$  @ V<sub>GS</sub>=4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

### Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

#### 100% UIS TESTED!

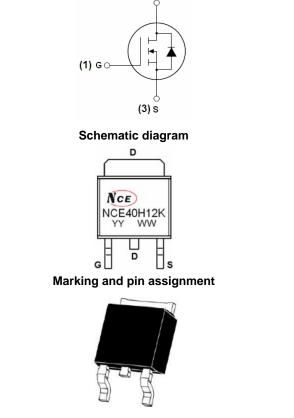
#### 100% ΔVds TESTED!

#### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40H12K	NCE40H12K	TO-252-2L	-	-	-

### Absolute Maximum Ratings (T<sub>c</sub>=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι <sub>D</sub>	120	А
Drain Current-Continuous(T <sub>C</sub> =100°C)	I <sub>D</sub> (100℃)	85	A
Pulsed Drain Current	I <sub>DM</sub>	330	A
Maximum Power Dissipation	PD	120	W
Derating factor		0.8	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	1080	mJ
Operating Junction and Storage Temperature Range	$T_J,T_STG$	-55 To 175	°C



(2) D

TO-252-2L top view





#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{ extsf{ heta}JC}$	1.25	°C/W

### Electrical Characteristics (T<sub>C</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	40	45	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA	
On Characteristics (Note 3)	·			•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	1.2	1.8	2.5	V	
Drain-Source On-State Resistance		V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	3.6	4.0		
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	-	5.8	7.0	- mΩ	
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =10V,I <sub>D</sub> =20A	26	-	-	S	
Dynamic Characteristics (Note4)	·		•				
Input Capacitance	C <sub>lss</sub>		-	5400	-	PF	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V, F=1.0MHz	-	970	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	380	-	PF	
Switching Characteristics (Note 4)	·			•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	15	-	nS	
Turn-on Rise Time	tr	$V_{DD}$ =20V, $I_D$ =2A, $R_L$ =1 $\Omega$	-	18	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> =10V,R <sub>G</sub> =3Ω	-	52	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	23	-	nS	
Total Gate Charge	Qg	)/ _20)// _20 /	-	75		nC	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =20V,I <sub>D</sub> =20A, V <sub>GS</sub> =10V	-	10.5		nC	
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	17		nC	
Drain-Source Diode Characteristics				•			
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =40A	-		1.2	V	
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	120	А	
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 40A	-	42	-	nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	45	-	nC	
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)					

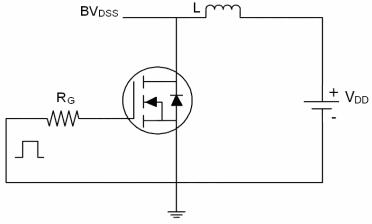
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- **5.** E<sub>AS</sub> condition : Tj=25 $^\circ C$  ,V<sub>DD</sub>=20V,V<sub>G</sub>=10V,L=1mH,Rg=25\Omega , I<sub>AS</sub>=46.5A

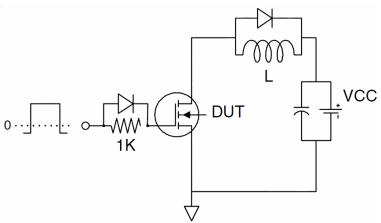




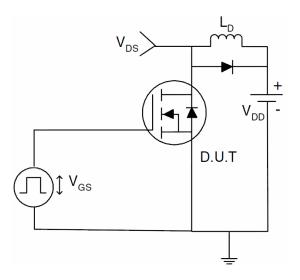
## Test circuit 1) E<sub>AS</sub> Test Circuit



## 2) Gate Charge Test Circuit



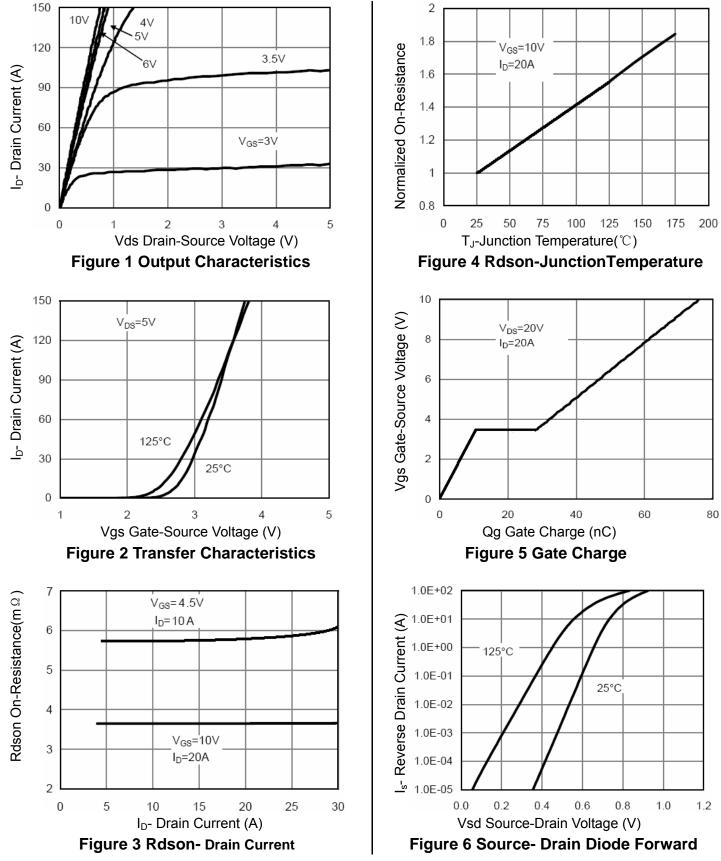
3) Switch Time Test Circuit





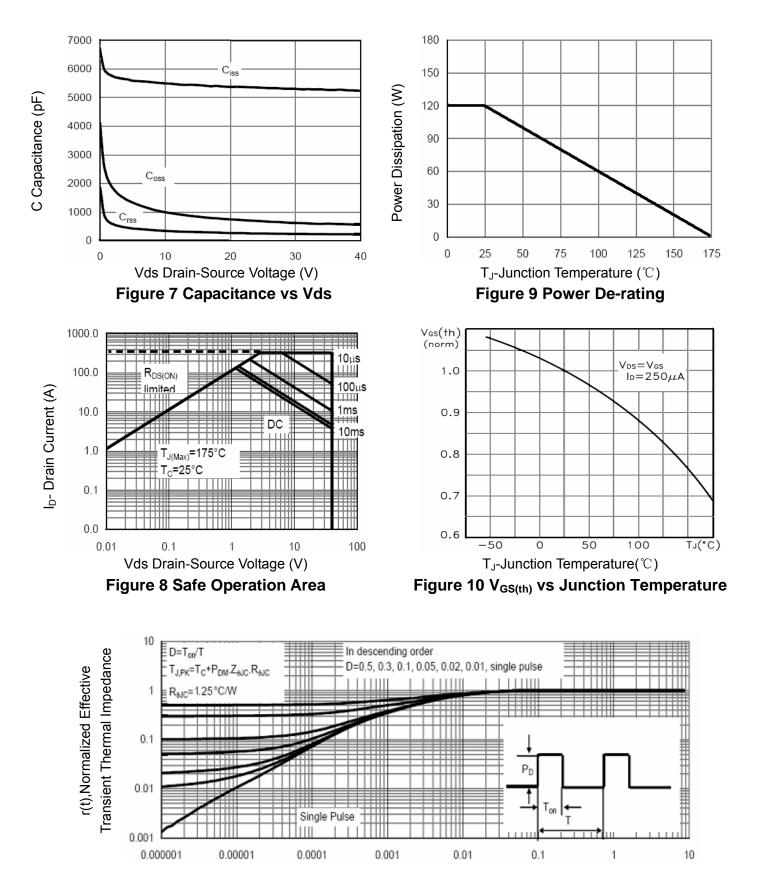


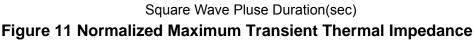








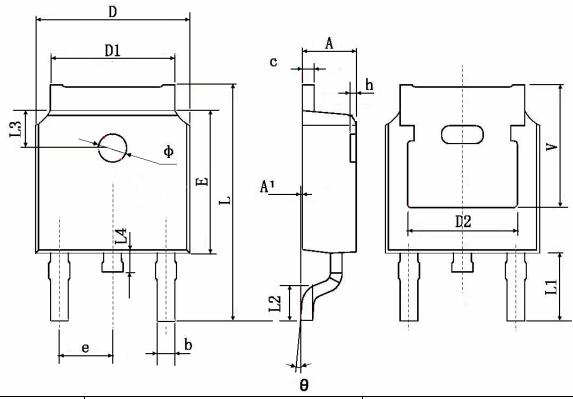








## **TO-252 Package Information**



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.83	0 TYP.	0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600	1.600 TYP.		TYP.	
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0 °	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211	TYP.	





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